

RJK1525DPS

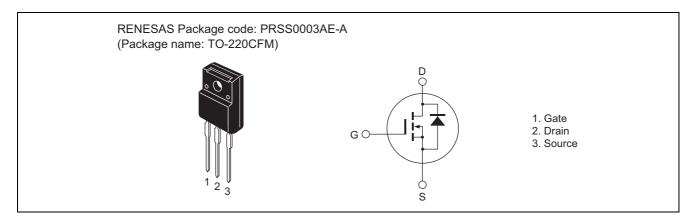
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1314-0200 Rev.2.00 Feb 08, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	150	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	17	Α
Drain peak current	I _{D (pulse)} Note1	50	Α
Body-drain diode reverse drain current	I _{DR}	17	Α
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	50	Α
Avalanche current	I _{AP} Note3	17	Α
Avalanche energy	E _{AR} Note3	21.6	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

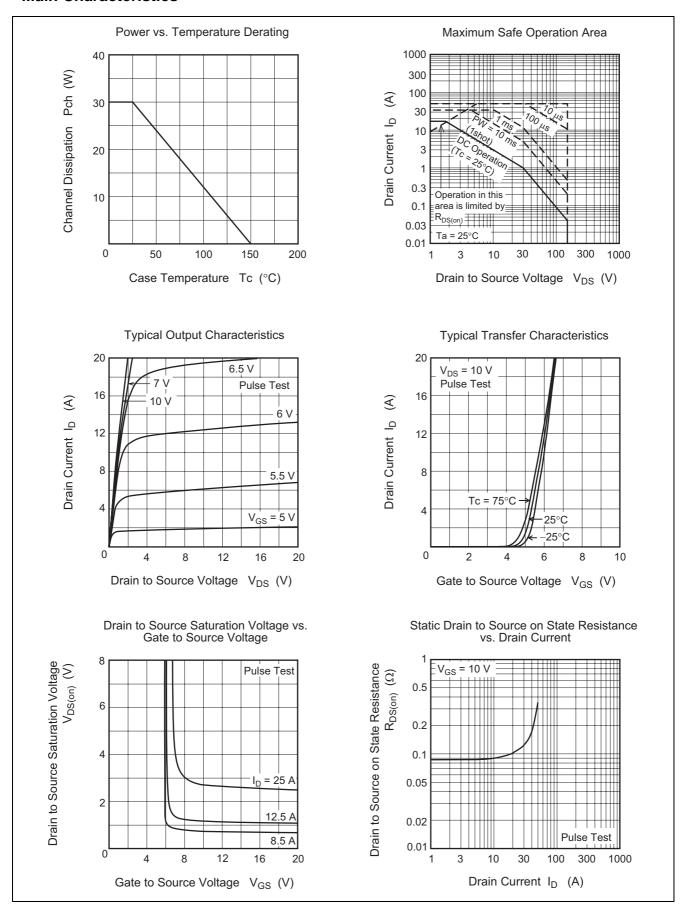
Electrical Characteristics

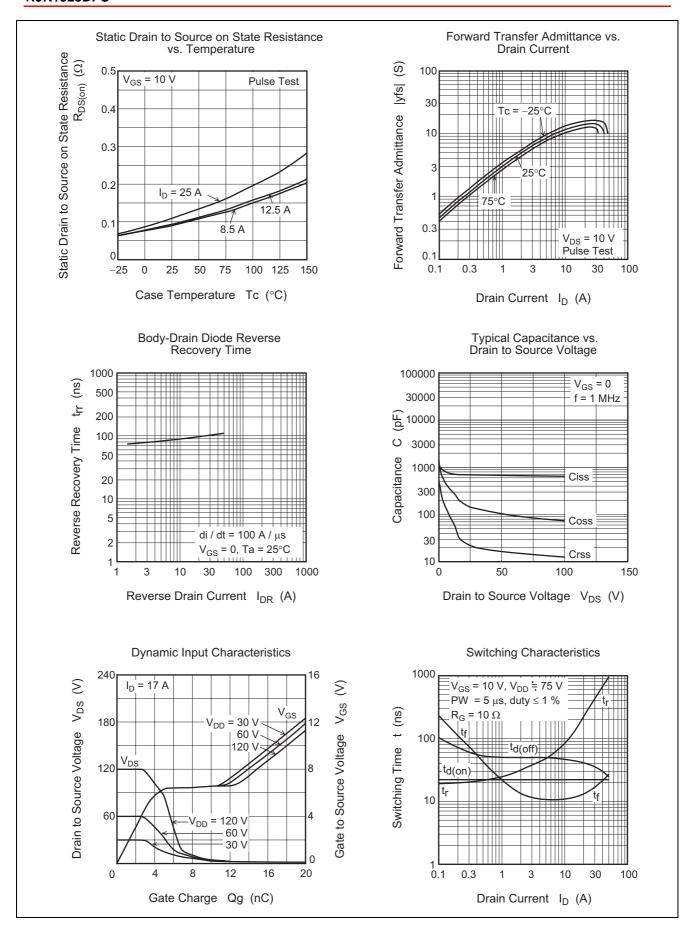
 $(Ta = 25^{\circ}C)$

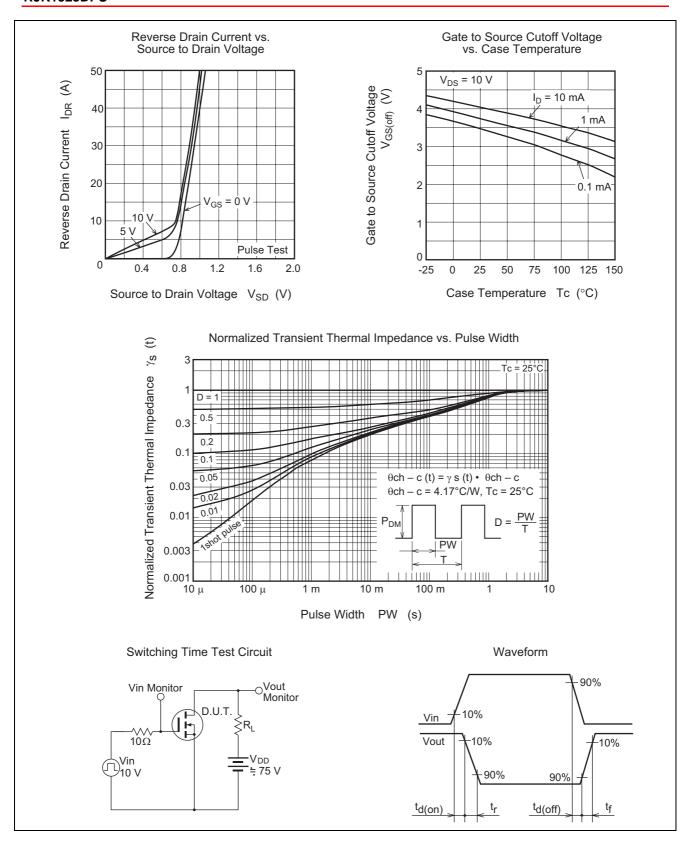
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 150 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y _{fs}	6	11	_	S	$I_D = 8.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Static drain to source on state resistance	R _{DS(on)}	_	0.089	0.110	Ω	$I_D = 8.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	680	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	150	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	22	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	22	_	ns	I _D = 8.5 A
Rise time	t _r	_	70	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	47	_	ns	$R_L = 8.8 \Omega$
Fall time	t _f	_	11	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	18	_	nC	V _{DD} = 120 V
Gate to source charge	Qgs	_	4.2	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	8.3	_	nC	I _D = 17 A
Body-drain diode forward voltage	V_{DF}	_	0.88	1.40	V	$I_F = 17 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}		95	_	ns	I _F = 17 A, V _{GS} = 0
Body-drain diode reverse recovery charge	Q _{rr}	_	0.3	_	μС	di _F /dt = 100 A/μs

Notes: 4. Pulse test

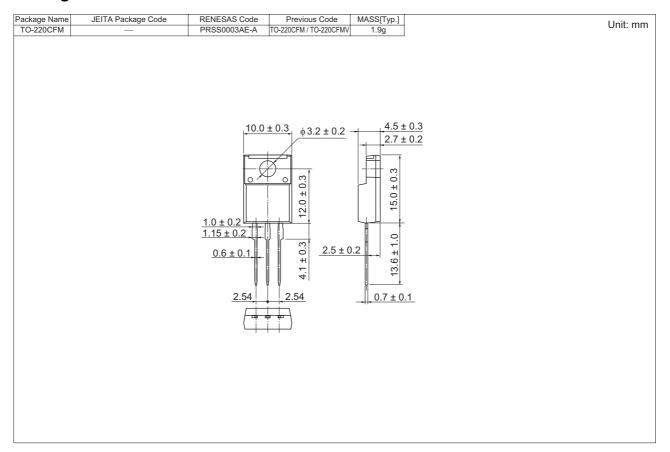
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1525DPS-00-T2	600 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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